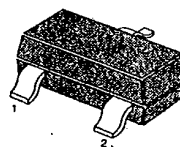


**MMBA812M6****PNP EPITAXIAL SILICON TRANSISTOR****GENERAL PURPOSE TRANSISTOR****ABSOLUTE MAXIMUM RATINGS ( $T_a = 25^\circ\text{C}$ )**

| Characteristic            | Symbol    | Rating | Unit             |
|---------------------------|-----------|--------|------------------|
| Collector-Base Voltage    | $V_{CB0}$ | 50     | V                |
| Collector-Emitter Voltage | $V_{CE0}$ | 40     | V                |
| Emitter-Base Voltage      | $V_{EB0}$ | 5      | V                |
| Collector Current         | $I_C$     | 100    | mA               |
| Collector Dissipation     | $P_C$     | 350    | mW               |
| Storage Temperature       | $T_{stg}$ | 150    | $^\circ\text{C}$ |

• Refer to MMBT5086 for graphs

SOT-23



1. Base 2. Emitter 3. Collector

**ELECTRICAL CHARACTERISTICS ( $T_a = 25^\circ\text{C}$ )**

| Characteristic                       | Symbol        | Test Condition                         | Min | Max | Unit |
|--------------------------------------|---------------|----------------------------------------|-----|-----|------|
| Collector Cutoff Current             | $I_{CBO}$     | $V_{CB} = 40\text{V}, I_E = 0$         |     | 100 | nA   |
| Emitter Cutoff Current               | $I_{EBO}$     | $V_{EB} = 5\text{V}, I_C = 0$          |     | 100 | nA   |
| DC Current Gain                      | $h_{FE}$      | $V_{CE} = 6\text{V}, I_C = 1\text{mA}$ | 200 | 400 |      |
| Collector-Emitter Saturation Voltage | $V_{CE(sat)}$ | $I_C = 30\text{mA}, I_B = 3\text{mA}$  |     | 0.5 | V    |
| Base-Emitter On Voltage              | $V_{BE(on)}$  | $I_C = 1\text{mA}, V_{CE} = 6\text{V}$ |     | 0.8 | V    |

Marking

